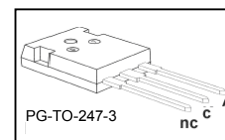


Fast Switching EmCon Diode

Features:

- 600 V EmCon technology
- Fast recovery
- Soft switching
- Low reverse recovery charge
- Low forward voltage
- 175 °C junction operating temperature
- Easy paralleling
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models:
<http://www.infineon.com/emcon/>



Applications:

- Welding
- Motor drives

Type	V_{RRM}	I_F	$V_F, T_J=25^\circ\text{C}$	$T_{J,max}$	Marking	Package
IDW100E60	600V	100A	1.65V	175°C	D100E60	PG-TO-247-3

Maximum Ratings

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	600	V
Continuous forward current	I_F		A
$T_C = 25^\circ\text{C}$		150	
$T_C = 90^\circ\text{C}$		104	
$T_C = 100^\circ\text{C}$		96	
Surge non repetitive forward current	I_{FSM}	400	A
$T_C = 25^\circ\text{C}$, $t_p = 10$ ms, sine halfwave			
Maximum repetitive forward current	I_{FRM}	300	A
$T_C = 25^\circ\text{C}$, t_p limited by $t_{j,max}$, $D = 0.5$			
Power dissipation	P_{tot}		W
$T_C = 25^\circ\text{C}$		375	
$T_C = 90^\circ\text{C}$		212	
$T_C = 100^\circ\text{C}$		198	
Operating junction and storage temperature	T_J, T_{stg}	-55...+175	°C
Soldering temperature	T_S	260	°C
1.6mm (0.063 in.) from case for 10 s			

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
Thermal resistance, junction – case	R_{thJC}		0.40	K/W
Thermal resistance, junction – ambient	R_{thJA}		40	

Electrical Characteristic, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	

Static Characteristic

Collector-emitter breakdown voltage	V_{RRM}	$I_R = 0.25\text{mA}$	600	-	-	V
Diode forward voltage	V_F	$I_F = 100\text{A}$	-	1.65	2.0	
		$T_j = 25^\circ\text{C}$ $T_j = 175^\circ\text{C}$	-	1.65	-	
Reverse leakage current	I_R	$V_R = 600\text{V}$	-	-	40	μA
		$T_j = 25^\circ\text{C}$ $T_j = 175^\circ\text{C}$	-	-	1000	

Dynamic Electrical Characteristics

Diode reverse recovery time	t_{rr}	$T_j = 25^\circ\text{C}$	-	120	-	ns
Diode reverse recovery charge	Q_{rr}	$V_R = 400\text{V}$,	-	3.6	-	μC
Diode peak reverse recovery current	I_{rr}	$I_F = 100\text{A}$,	-	49.5	-	A
Diode peak rate of fall of reverse recovery current during t_b	dl_{rr}/dt	$dl_F/dt = 1200\text{A}/\mu\text{s}$	-	750	-	$\text{A}/\mu\text{s}$

Diode reverse recovery time	t_{rr}	$T_j = 125^\circ\text{C}$	-	168	-	ns
Diode reverse recovery charge	Q_{rrm}	$V_R = 400\text{V}$,	-	5.8	-	μC
Diode peak reverse recovery current	I_{rr}	$I_F = 100\text{A}$,	-	61.6	-	A
Diode peak rate of fall of reverse recovery current during t_b	dl_{rr}/dt	$dl_F/dt = 1200\text{A}/\mu\text{s}$	-	705	-	$\text{A}/\mu\text{s}$

Diode reverse recovery time	t_{rr}	$T_j = 175^\circ\text{C}$	-	200	-	ns
Diode reverse recovery charge	Q_{rrm}	$V_R = 400\text{V}$,	-	7.8	-	μC
Diode peak reverse recovery current	I_{rr}	$I_F = 100\text{A}$,	-	67.0	-	A
Diode peak rate of fall of reverse recovery current during t_b	dl_{rr}/dt	$dl_F/dt = 1200\text{A}/\mu\text{s}$	-	650	-	$\text{A}/\mu\text{s}$

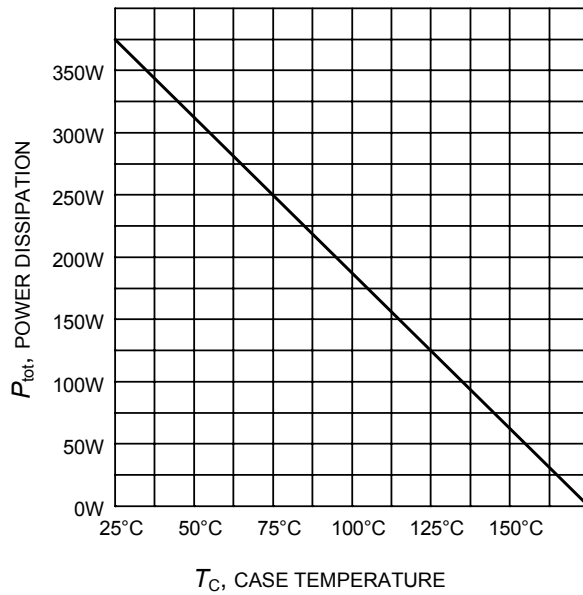


Figure 1. Power dissipation as a function of case temperature ($T_j \leq 175^\circ\text{C}$)

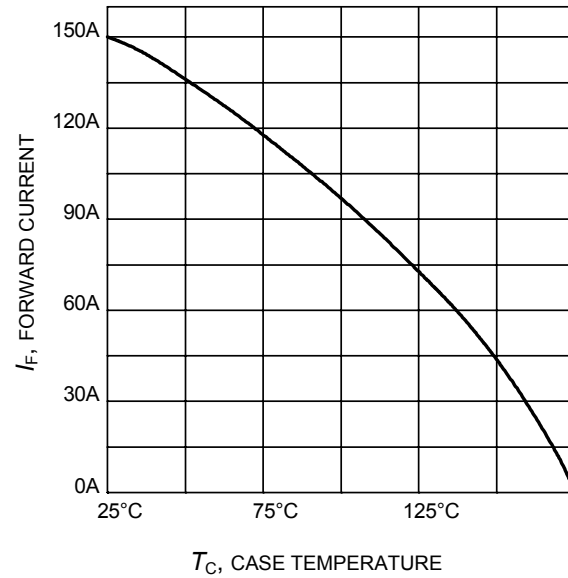


Figure 2. Diode forward current as a function of case temperature ($T_j \leq 175^\circ\text{C}$)

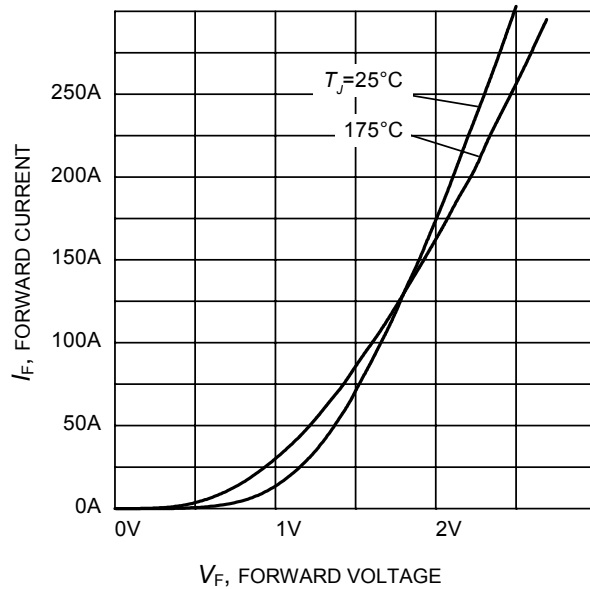


Figure 3. Typical diode forward current as a function of forward voltage

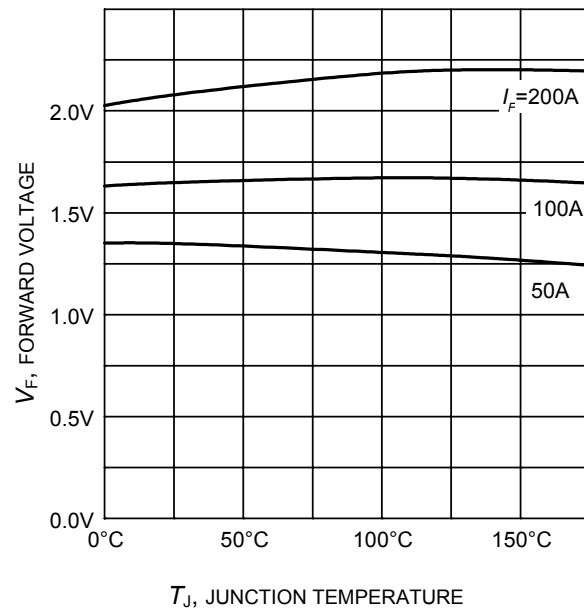


Figure 4. Typical diode forward voltage as a function of junction temperature

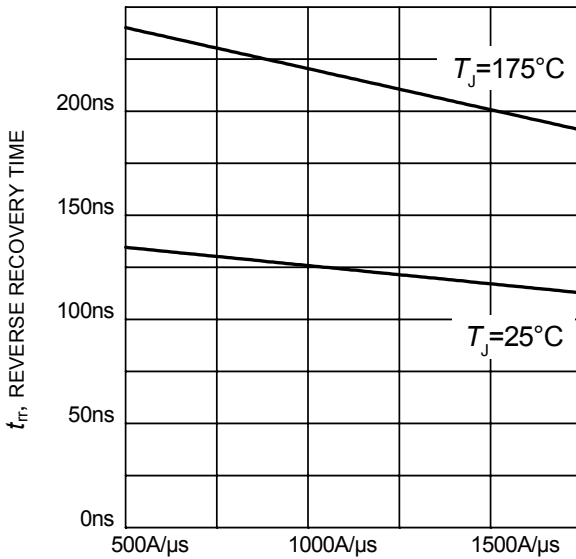

 di_F/dt , DIODE CURRENT SLOPE

Figure 5. Typical reverse recovery time as a function of diode current slope
($V_R=400V$, $I_F=100A$,
Dynamic test circuit in Figure E)

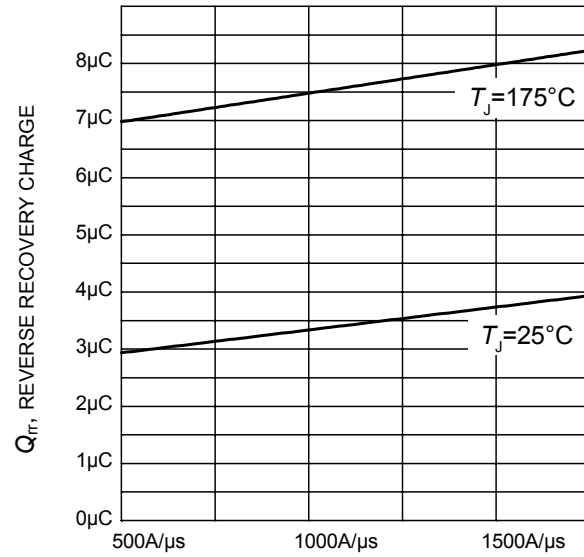

 di_F/dt , DIODE CURRENT SLOPE

Figure 6. Typical reverse recovery charge as a function of diode current slope
($V_R=400V$, $I_F=100A$,
Dynamic test circuit in Figure E)

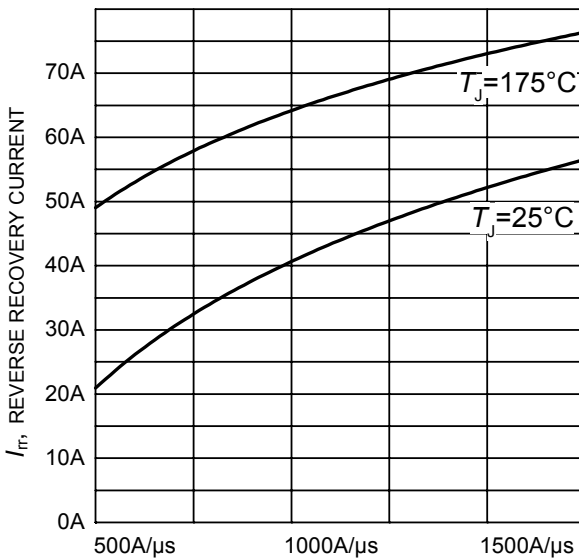

 di_F/dt , DIODE CURRENT SLOPE

Figure 7. Typical reverse recovery current as a function of diode current slope
($V_R=400V$, $I_F=100A$,
Dynamic test circuit in Figure E)

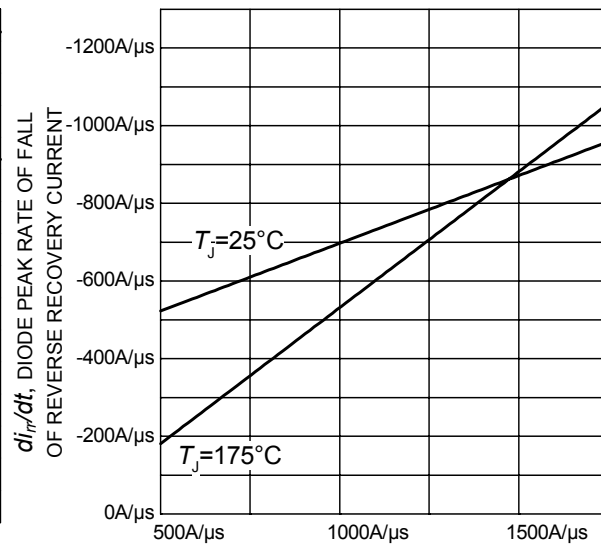

 di_F/dt , DIODE CURRENT SLOPE

Figure 8. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope
($V_R=400V$, $I_F=100A$,
Dynamic test circuit in Figure E)

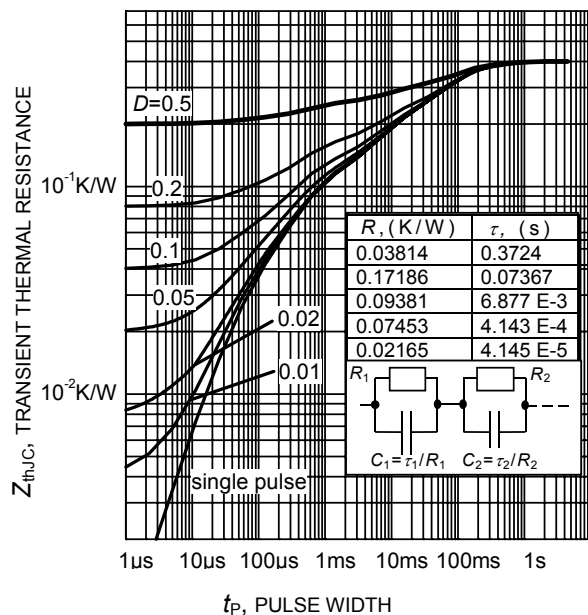
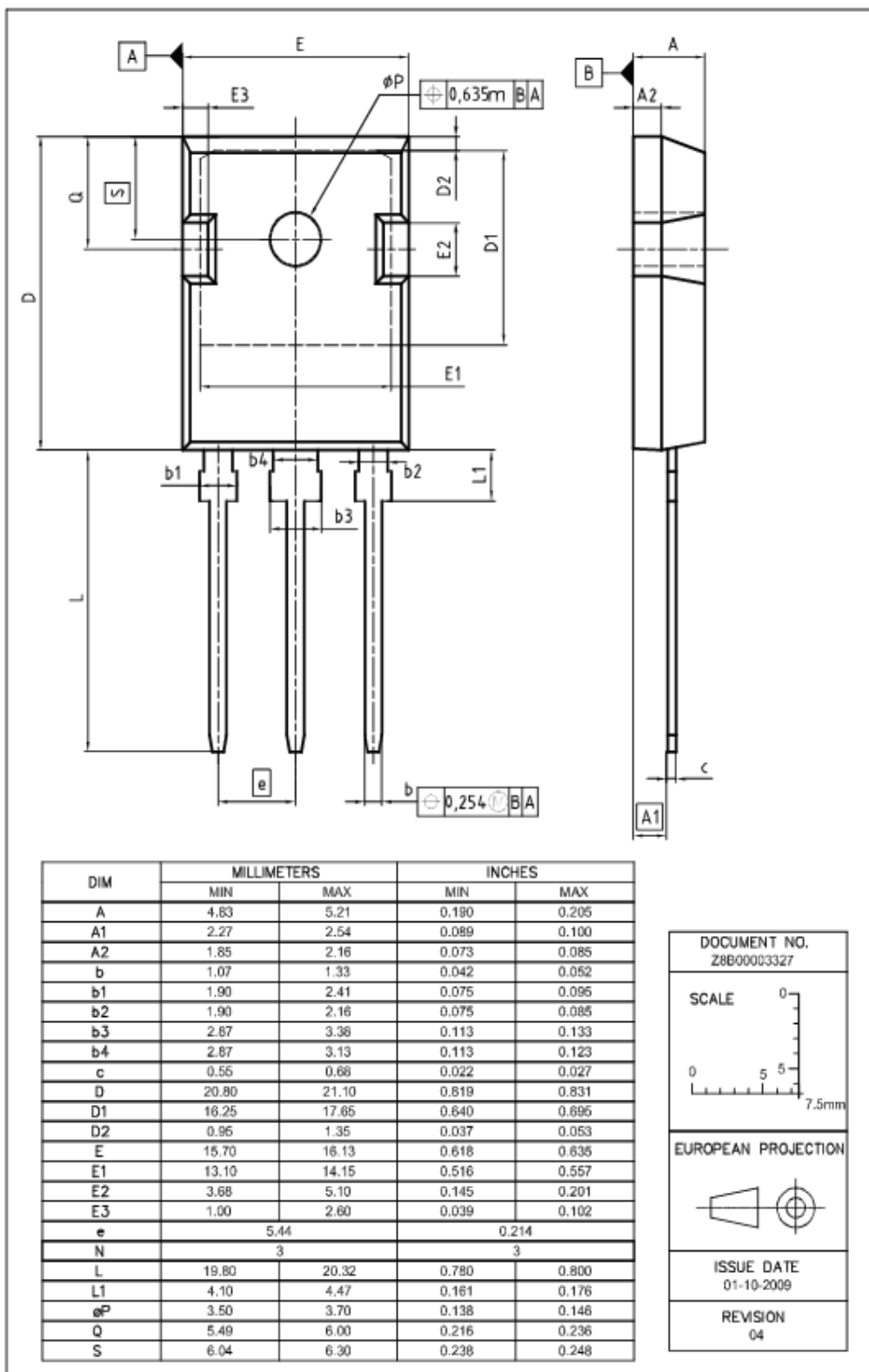


Figure 9. Diode transient thermal impedance as a function of pulse width
 $(D=t_p/T)$

T0247-3



Published by
Infineon Technologies AG
81726 Munich, Germany
© 2008 Infineon Technologies AG
All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office. Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.